### TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

# S2000AF

COLOR TV HORIZONTAL OUTPUT APPLICATIONS
COLOR TV SWITCHING REGULATOR APPLICATIONS

• High Voltage :  $V_{CES} = 1500 V$ • High Speed :  $t_f = 0.7 \mu s$  (Max.)

• Low Saturation Voltage :  $V_{CE (sat)} = 5 V (Max.)$ 

• Collector Metal (Fin) is Fully Covered with Mold Resin. ((IS) Package)

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		V <sub>CES</sub>	1500	V	
Emitter-Base Voltage		$V_{EBO}$	5	V	
Collector Current	DC	IC	8	A	
	Pulse	ICP	15		
Base Current		$I_{\mathbf{B}}$	4	A	
Collector Power Dissipation (Tc = 25°C)		PC	50	w	
Junction Temperature		$T_{j}$	150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	
Thermal Resistance		R <sub>th (j-c)</sub>	2.5	°C/W	

Unit in mm

15.5±0.5 Ø3.6±0.3 3.0±0.3

15.5±0.5 Ø3.6±0.3 3.0±0.3

2.3MAX 0.95MAX 0.95M

Weight: 5.5 g (Typ.)

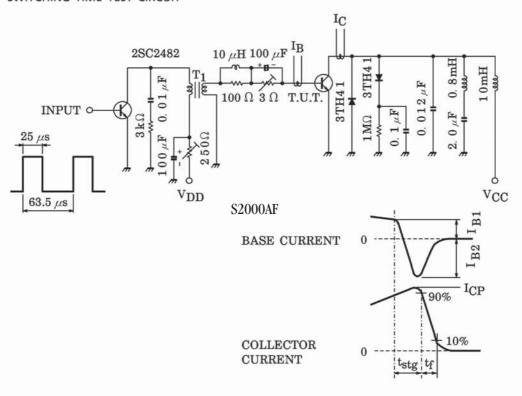
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 1500 \text{ V}, V_{BE} = 0$	_	_	1	mA
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	$I_{\mathrm{E}}=1\mathrm{mA},~I_{\mathrm{C}}=0$	5	_	_	V
DC Current Gain	h <sub>FE</sub> (1)	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	10	_	30	
	h <sub>FE</sub> (2)	$V_{CE} = 5 V, I_{C} = 4.5 A$	4.5	_	9	
Collector-Emitter Saturation	V ~	$I_C = 4.5 \text{ A}, I_B = 2 \text{ A}$	_	<del>-</del>	1	v
Voltage	VCE (sat)	$I_C = 4.5 \text{ A}, I_B = 1 \text{ A}$	_	_	5	٧
Base-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	$I_{C} = 4.5 \text{ A}, I_{B} = 1 \text{ A}$	_	0.9	1.2	v
Collector-Emitter Sustain Voltage	V <sub>CEX</sub> (sus)	$L = 40 \text{ mH}, I_{\text{B}} = 500 \text{ mA}$ $V_{\text{BE}} = -1.7 \text{ V}$	700	-	_	V
Transition Frequency	$ m f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}$	_	2	-	MHz
Collector Output Capacitance	Cob	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	95		рF
Switching Time Storage Time	$t_{\mathrm{stg}}$	$I_{CP} = 4.5 \text{ A}, I_{B1} \text{ (end)} = 1 \text{ A}$	_	8	12	
(Fig.1) Fall Time	tf	$ m f_{H} = 15.75  kHz$	_	0.4	0.7	$\mu$ s

#### 961001EAA2

<sup>●</sup> TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

Fig.1 SWITCHING TIME TEST CIRCUIT



Base Current Gradient

$$\mathrm{dI}_B/\,\mathrm{dt} = \, \frac{\mathrm{I}_{B1} + \mathrm{I}_{B2}}{t_{stg}} \, (\mathrm{A} \, / \, \mu \mathrm{s})$$

961001EAA2

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
 The information contained herein is subject to change without notice.